

L Number	Hits	Search Text	DB	Time stamp
1	795	438/682	USPAT	2004/05/24 16:57
2	485	438/681	USPAT	2004/05/24 16:57
3	962	438/683	USPAT	2004/05/24 16:57
4	288	438/684	USPAT	2004/05/24 16:58
5	998	438/680	USPAT	2004/05/24 16:58
6	777	438/649	USPAT	2004/05/24 16:58
7	259	438/650	USPAT	2004/05/24 16:58
8	259	438/651	USPAT	2004/05/24 16:58
9	1194	438/655	USPAT	2004/05/24 16:58
10	1273	438/656	USPAT	2004/05/24 16:58
11	460	438/657	USPAT	2004/05/24 16:58
12	370	438/668	USPAT	2004/05/24 16:58
13	262	438/721	USPAT	2004/05/24 16:58
14	99	438/755	USPAT	2004/05/24 16:58
15	266	438/510	USPAT	2004/05/24 16:58
16	647	438/514	USPAT	2004/05/24 16:59
17	76	438/914	USPAT	2004/05/24 16:59
18	151	438/954	USPAT	2004/05/24 16:59
19	1283	438/197	USPAT	2004/05/24 16:59
20	494	438/276	USPAT	2004/05/24 16:59
21	810	438/300	USPAT	2004/05/24 16:59
22	1779	438/301	USPAT	2004/05/24 16:59
23	1859	438/303	USPAT	2004/05/24 16:59
24	406	438/304	USPAT	2004/05/24 16:59
25	332	438/311	USPAT	2004/05/24 16:59
26	215	438/733	USPAT	2004/05/24 16:59
	0	10/700779	USPAT	2004/05/24 11:15
	0	ILD and interlevel and dielectric and electrode and gate and spacer and side and wall and gap and gaps and silicide and salicide and source and drain and polysilicon and thickness and ion and p-type and n-type and channel and region and LDD and lightly and doped	USPAT	2004/05/24 11:20
	0	ILD and interlevel and dielectric and electrode and gate and spacer and side and wall and silicide and salicide and source and drain and polysilicon and thickness and ion and p-type and n-type and channel and region and LDD and lightly and doped	USPAT	2004/05/24 11:21
	0	ILD and interlevel and dielectric and electrode and gate and spacer and side and wall and silicide and salicide and source and drain and polysilicon and thickness and ion and gap and channel and region and LDD and lightly and doped	USPAT	2004/05/24 11:24
	0	ILD and dielectric and electrode and gate and spacer and side and wall and silicide and salicide and source and drain and polysilicon and thickness and ion and void and channel and region and LDD and lightly and doped	USPAT	2004/05/24 11:24
	1	ILD and dielectric and electrode and gate and spacer and side and wall and silicide and source and drain and polysilicon and thickness and ion and void and channel and region and LDD and lightly and doped	USPAT	2004/05/24 11:23
	1		USPAT	2004/05/24 11:23
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	1	ILD and dielectric and electrode and gate and spacer and side and wall and silicide and source and drain and polysilicon and thickness and ion and void and channel and region and LDD and lightly and doped	USPAT	2004/05/24 11:24
	1	ILD and interlevel and dielectric and electrode and gate and spacer and side and wall and gap and gaps and silicide and source and drain and polysilicon and thickness and ion and p-type and n-type and channel and region and LDD and lightly and doped	USPAT	2004/05/24 11:24

-	1		USPAT	2004/05/24 11:26
-	1		USPAT	2004/05/24 11:26
-	1		USPAT	2004/05/24 11:26
-	1		USPAT	2004/05/24 11:27
-	1	("5751040").PN.	USPAT	2004/05/24 11:27
-	1	("4994404").PN.	USPAT	2004/05/24 11:27
-	1	("6365943").PN.	USPAT	2004/05/24 11:27
-	1	("6380535").PN.	USPAT	2004/05/24 11:28
-	1	("6455373").PN.	USPAT	2004/05/24 11:28
-	1	ILD and interlevel and dielectric and electrode and gate and spacer and side and wall and gap and gaps and silicide and source and drain and polysilicon and thickness and ion and p-type and n-type and channel and region and LDD and lightly and doped	USPAT	2004/05/24 11:29
-	0	ILD and interlevel and dielectric and electrode and gate and spacer and side and wall and gap and gaps and silicide and source and drain and polysilicon and thickness and ion and p-type and n-type and channel and region and LDD and lightly and doped	USPAT	2004/05/24 11:29
-	1	(ILD and interlevel and dielectric and electrode and gate and spacer and side and wall and gap and gaps and silicide and source and drain and polysilicon and thickness and ion and p-type and n-type and channel and region and LDD and lightly and doped) and (sidewall or spacer or gap or gaps or void or closely or thickness or cobalt or nickel or titanium or polysilicon or contact or area or region or rate or aspect or ratio or silicide or silicide or n-type or p-type or channel or lightly or doped or LDD or etch or anisotropically or back or angstroms)	USPAT	2004/05/24 16:57
-	1	(ILD and dielectric and electrode and gate and spacer and side and wall and silicide and source and drain and polysilicon and thickness and ion and void and channel and region and LDD and lightly and doped) and (sidewall or spacer or gap or gaps or void or closely or thickness or cobalt or nickel or titanium or polysilicon or contact or area or region or rate or aspect or ratio or silicide or silicide or n-type or p-type or channel or lightly or doped or LDD or etch or anisotropically or back or angstroms)	USPAT	2004/05/24 11:38

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